



YOUSHANG SEMICONDUCTOR

设计研发新型功率器件

各类小信号开关

中低压及高压大电流等场效应管

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企业微信二维码



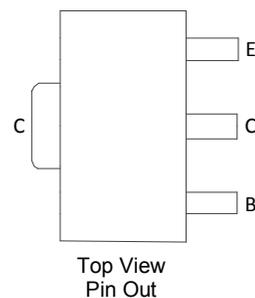
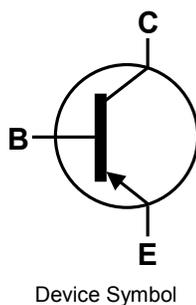
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Features

- $BV_{CEO} > -150V$
- $I_C = -600mA$ Continuous Current
- Low Saturation Voltage $V_{CE(sat)} < -0.5V @ -50mA$
- $P_D = 1.2W$ Power Dissipation
- Complementary part number NK-ZXTN5551Z

Mechanical Data

- Case: SOT89
- Case Material: Molded Plastic. "Green" Molding Compound. UL Flammability Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals: Finish - Matte Tin Plated Leads, Solderable per MIL-STD-202, Method 208 ③
- Weight: 0.05 grams (Approximate)



Absolute Maximum Ratings (@ $T_A = +25^\circ\text{C}$, unless otherwise specified.)

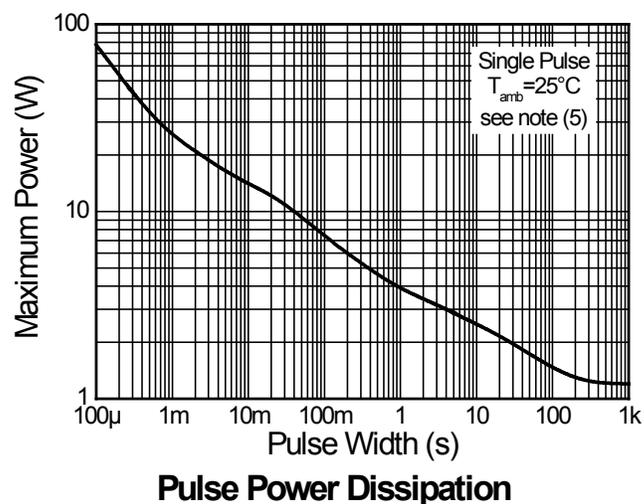
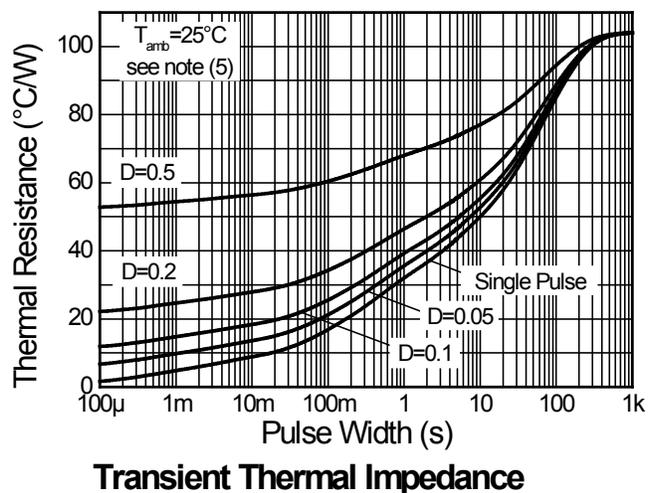
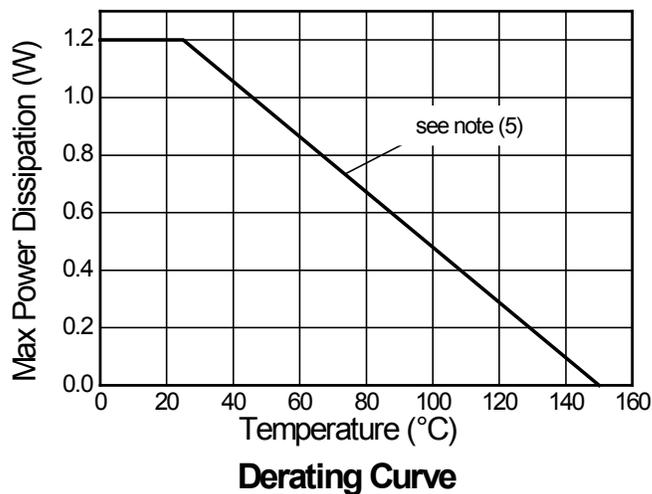
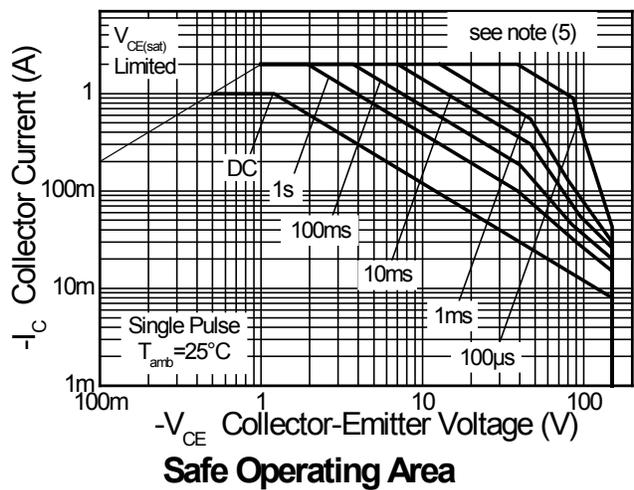
Characteristic	Symbol	Value	Unit
Collector-Base Voltage	V_{CBO}	-160	V
Collector-Emitter Voltage	V_{CEO}	-150	V
Emitter-Base Voltage	V_{EBO}	-5	V
Continuous Collector Current	I_C	-600	mA
Peak Pulse Collector Current (single pulse)	I_{CM}	-2	A

Thermal Characteristics (@ $T_A = +25^\circ\text{C}$, unless otherwise specified.)

Characteristic	Symbol	Value	Unit
Power Dissipation (Note 5)	P_D	1.2	W
Linear Derating Factor	—	9.6	mW/ $^\circ\text{C}$
Thermal Resistance, Junction to Ambient (Note 5)	$R_{\theta JA}$	—	$^\circ\text{C/W}$
Operating and Storage Temperature Range	T_J, T_{STG}	-55 to +150	$^\circ\text{C}$

Note: 5. For a device surface mounted on 25mm x 25mm x 1.6mm FR4 PCB with high coverage of single sided 1oz weight copper, in still air conditions.

Thermal Characteristics and Derating Information

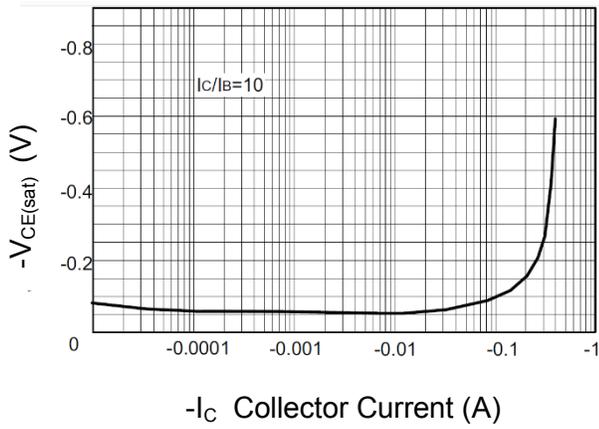


Electrical Characteristics (@ $T_A = +25^\circ\text{C}$, unless otherwise specified.)

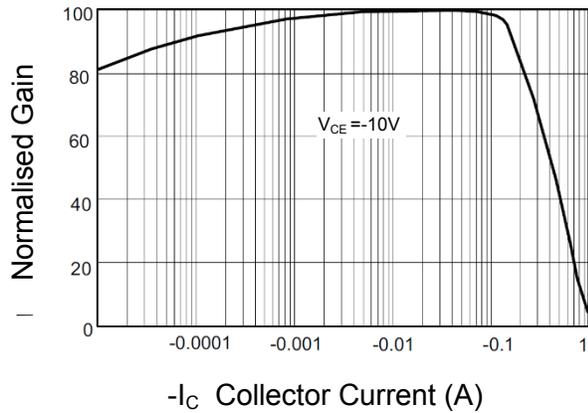
Characteristic	Symbol	Min	Typ	Max	Unit	Test Condition
Collector-Base Breakdown Voltage	BV_{CBO}	-160	-270	—	V	$I_C = -100\mu\text{A}$
Collector-Emitter Breakdown Voltage	BV_{CEO}	-150	-240	—	V	$I_C = -1\text{mA}$
Emitter-Base Breakdown Voltage	BV_{EBO}	-5	-8.1	—	V	$I_E = -100\mu\text{A}$
Collector Cut-Off Current	I_{CBO}	—	-1	-50	nA μA	$V_{CB} = -120\text{V}$ $V_{CB} = -120\text{V}, T_A = +100^\circ\text{C}$
Collector-Emitter Saturation Voltage (Note 6)	$V_{CE(sat)}$	—	-50	-200	mV mV	$I_C = -10\text{mA}, I_B = -1\text{mA}$ $I_C = -50\text{mA}, I_B = -5\text{mA}$
Base-Emitter Saturation Voltage (Note 6)	$V_{BE(sat)}$	—	-700	-1000	mV mV	$I_C = -10\text{mA}, I_B = -1\text{mA}$ $I_C = -50\text{mA}, I_B = -5\text{mA}$
DC current gain (Note 6)	h_{FE}	50	135	—	—	$I_C = -1\text{mA}, V_{CE} = -5\text{V}$ $I_C = -10\text{mA}, V_{CE} = -5\text{V}$ $I_C = -50\text{mA}, V_{CE} = -5\text{V}$
Transitional frequency	f_T	—	100	—	MHz	$I_C = -10\text{mA}, V_{CE} = -10\text{V}$, $f = 100\text{MHz}$
Output Capacitance	C_{obo}	—	—	6	pF	$V_{CB} = -10\text{V}, f = 1\text{MHz}$
Delay time	t_d	—	386	—	ns	$V_{CC} = -10\text{V}, I_C = -100\text{mA}$, $I_{B1} = -I_{B2} = -10\text{mA}$
Rise time	t_r	—	202	—	ns	
Storage time	t_s	—	1720	—	ns	
Fall time	t_f	—	275	—	ns	

 Note: 6. Measured under pulsed conditions. Pulse width $\leq 300\mu\text{s}$. Duty cycle $\leq 2\%$.

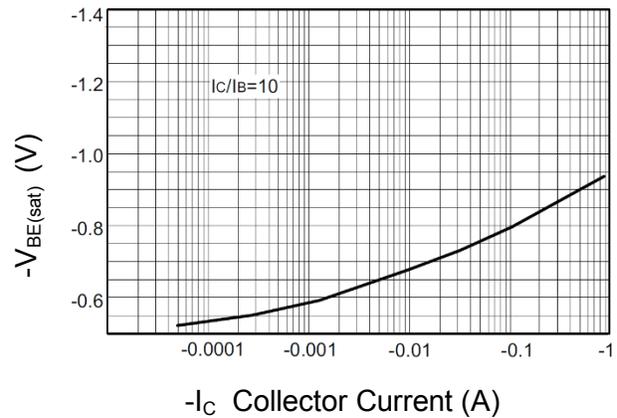
Typical Electrical Characteristics (@ $T_A = +25^\circ\text{C}$, unless otherwise specified.)



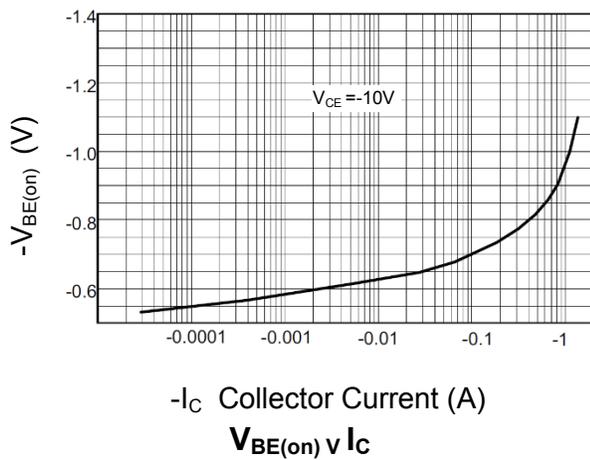
$V_{CE(sat)} \text{ v } I_C$



$h_{FE} \text{ v } I_C$

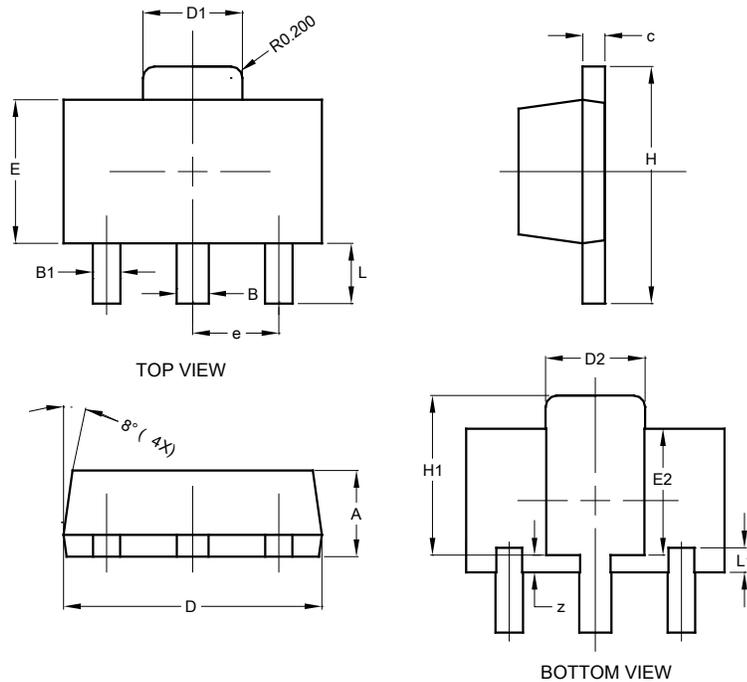


$V_{BE(sat)} \text{ v } I_C$



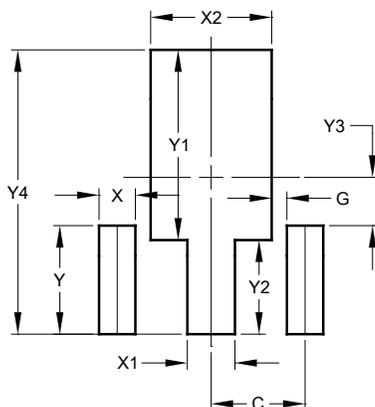
$V_{BE(on)} \text{ v } I_C$

Package Outline Dimensions

SOT89


SOT89			
Dim	Min	Max	Typ
A	1.40	1.60	1.50
B	0.50	0.62	0.56
B1	0.42	0.54	0.48
c	0.35	0.43	0.38
D	4.40	4.60	4.50
D1	1.62	1.83	1.733
D2	1.61	1.81	1.71
E	2.40	2.60	2.50
E2	2.05	2.35	2.20
e	-	-	1.50
H	3.95	4.25	4.10
H1	2.63	2.93	2.78
L	0.90	1.20	1.05
L1	0.327	0.527	0.427
z	0.20	0.40	0.30
All Dimensions in mm			

Suggested Pad Layout

SOT89


Dimensions	Value (in mm)
C	1.500
G	0.244
X	0.580
X1	0.760
X2	1.933
Y	1.730
Y1	3.030
Y2	1.500
Y3	0.770
Y4	4.530